



#### The Filmetrics Advantage

- World's leader in tabletop thin-film measurement
- 24-hour phone, e-mail, and online support
- Intuitive analysis software standard with every system

#### Additional Features

- Built-in online diagnostics
- Standalone software included
- Sophisticated history function for saving, reproducing, and plotting results

## Automated Thin-Film Thickness Mapping System

Thin-film thickness of samples up to 450 mm in diameter are mapped quickly and easily with the F54 advanced spectral reflectance system. The motorized r-theta stage moves automatically to selected measurement points and provides thickness measurements as fast as two points per second. The F54 has the same precision high-lifetime stage that performs millions of measurements in our production systems.

Choose one of dozens of predefined polar, rectangular, or linear map patterns, or create your own with no limit on the number of measurement points. The entire desktop system is set up in minutes and can be used by anyone with basic computer skills.

### **Example Layers**

Virtually any smooth, non-metallic film may be measured. Examples include:

SiO <sub>2</sub>	SiN <sub>x</sub>	DLC	Polysilicon
Photoresist	Polymer Layers	Polyimide	Amorphous Silicon

## **Example Applications**

Semiconductor Fabrication	LCD			
Photoresist	Cell Gaps			
Oxides/Nitrides/SOI	Polyimide			
Wafer Backgrinding	ITO			
MEMS	Optical Coatings			
Photoresist	Hardness Coatings			
Silicon Membranes	Anti-Reflection Coating			
AIN/ZnO Thin-Film Filter	Filters			



# **F54** Thin-Film Mapping Analyzer



Measurement Specifications	F54-UV	F54-	UVX	F5	4	F54-EXR	F	F54-NIR		
Thickness Range with 5X Objective*:	-	-		20nm-40µm		20nm-120µ	m 100r	100nm-120µm		
Thickness Range with 10X Objective*1:	4nm-35µm	4nm-115µm		20nm-45µm		20nm-115µ	m 100r	100nm-115µm		
Thickness Range with 15X Objective*1:	4nm-30µm	4nm-100µm		20nm-40µm		20nm-100µ	m 100r	100nm-100µm		
Thickness Range with 50X Objective*:	-			20nm-2µm		20nm-4µm	n 100	100nm-4µm		
Min. Thickness to Measure n and k $^{\star 2}\!\!:$	50 nm	50 nm		100 nm		100 nm	5	500 nm		
Accuracy*: The Greater of	1 nm or 0.2%	1 nm or 0.2%		2 nm or 0.2%		2 nm or 0.2	% 3 nr	3 nm or 0.4%		
Precision <sup>3</sup> :	0.02 nm	0.02 nm		0.2 nm		0.02 nm	(	0.1 nm		
Stability⁴:	0.05 nm	0.05 nm		0.05	nm	0.05 nm	0	.12 nm		
General Specifications										
Spectrometer Wavelength Range:	190-1100 nm	190-1700 nm		380-10	50 nm	380-1700 nm 950		-1700 nm		
Light Source:	External D2	gen	Internal Halogen							
Dimensions:	14W x 19D x 22H (in) 35.5W x 48.3D x 55H (cm)									
Weight:	41 lbs. (19 kg)									
Power Requirements:	100 - 240 VAC 50 - 60 Hz 230 W									
Computer Requirements			Spot Size		500 µm	250 µm	100 µm	50 μm Aperture		
Processor Clock Speed:	1.4 GHz min		5X Objective:		100 um	50 um	20 um	10 um		
Interface:	USB 2.0		10X Objective:		50 um	25 um	10 µm	5 um		
Operating System			15X Objective:		33 um	17 μm	7 um	3.5 um		
PC: Windows XP (SP2) - Latest Windows (64-bit)			50X Objective:		10 µm	5 um	2 um	1.um		
Mac: OS X Lion - Latest Mac OS running Parallels				JUX Objective.		Chuck	2 µm	2 µiii i µiii		
* Material and microscope dependent <sup>1</sup> Reflective objective <sup>2</sup> Using 5X objective			Sample Size:		< 200 mm diameter		< 300 mm diamotor			
<sup>3</sup> 1σ of 100 measurements of 1 μm SiO <sub>2</sub> -on-Si. Value is average of 1σ over 20 days. <sup>4</sup> 2σ of daily average of 100 measurements of 1 μm SiO,-on-Si,			Speed (Typical with Vacuum Chuck):		5 points - 5 sec. 25 points - 14 sec. 56 points - 29 sec.		5 point 25 point 56 point	5 points - 8 sec. 25 points - 21 sec. 56 points - 43 sec.		

 $^42\sigma$  of daily average of 100 measurements of 1  $\mu$ m SiO<sub>2</sub>-on-Si, measured over 20 days.



